In re Applicat	on of: Jum Soo KIM et al.)	
Application N	o.: 10/029,394)	Group Art Unit: 2812
Filed: Decem	ber 28, 2001)	Examiner: not yet assigned
	OD OF MANUFACTURING ADDRESS MEMORY CELL))	

PATENT

Commissioner for Patents Washington, D.C. 20231

		PRELIMINARY AMENDMENT TRANSMITTAL FORM			
1.	Trai	nsmitted herewith is a Preliminary Amendment.). JC - ,TC		
2.	Add	Additional papers enclosed.		. A	<u> </u>
		Drawings: [] Formal [] Informal (Correction) Information Disclosure Statement Form PTO-1449, references included Citations Declaration of Biological Deposit Submission of "Sequence Listing", computer readable copy and/or as pertaining thereto for biotechnology invention containing nucleotide acid sequence			ECEIVED ino

Page 2

3. Extension of Time

The proceedings herein are for a patent application and the provisions of 37 CFR 1.136(a) apply.

- [X] Applicants believe that no extension of time is required. However, this conditional petition is being made to provide for the possibility that applicant has inadvertently overlooked the need for a petition and fee for extension of time.
- [] Applicants petition for an extension of time, the fees for which are set out in 37 CFR 1.17(a)-(d), for the total number of months checked below:

Total Months Requested	Fee for Extension	[Fee for Small Entity]
[] one month	\$ 110.00	\$ 55.00
[] two months	\$ 400.00	\$200.00
[] three months	\$ 920.00	\$460.00
[] four months	\$1,440.00	\$720.00

If an additional extension of time is required, please consider this a Petition therefor.

[] An extension for __ months has already been secured and the fee paid therefor of \$___ is deducted from the total fee due for the total months of extension now requested.

4. Constructive Petition

[X] EXCEPT for issue fees payable under 37 C.F.R. § 1.18, the Commissioner is hereby authorized by this paper to charge any additional fees during the entire pendency of this application including fees due under 37 C.F.R. §§ 1.16 and 1.17 which may be required, including any required extension of time fees, or credit any overpayment to Deposit Account 50-0310. This paragraph is intended to be a CONSTRUCTIVE PETITION FOR EXTENSION OF TIME in accordance with 37 C.F.R. § 1.136(a)(3).

ATTORNEY DOCKET NO.: 054216-5016

Application Serial No.: 10/029,394

Page 3

5. Fee Calculation (37 C.F.R. §1.16)

CLAIMS AS AMENDED						
	Claims Remaining After Amendment		Highest No. Previously Paid	Present Extra	at Rate of	Total Fees
Total Claims (37 C.F.R. §1.16(c))	12	Minus	20	0	x \$18.00 each=	+ \$ 0.00
Independent Claims (37 C.F.R.§1.16(b))	2	Minus	3	0	x \$84.00 each=	+ \$ 0.00
[] First presentation of Multiple dependent claim(s) \$280.00 +\$				+ \$		
SUB-TOTAL = \$0.00						
Reduction by 1/2 for filing by a small entity-\$						
TOTAL FEE = \$ 0.00						

6.	Fee	Pay	ment

[X]	No fee is to be paid at this time.				
[]	Please charge our Deposit Account No. 50-0310 in the amount of				
	\$ for the fee.				
[X]	The Commissioner is hereby authorized to charge any additional fees including fees due under 37 CFR §1.16 and §1.17 which may be required, or credit any overpayment to Deposit Account 50-0310.				
	Respectfully submitted,				

Dated: April 3, 2002

By:

Sam Bhattacharya

Reg. No. 48,107

MORGAN, LEWIS & BOCKIUS LLP

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In re Application of: Jum Soo KIM et al.)
Application No.: 10/029,394) Group Art Unit: 2812
Filed: December 28, 2001	Examiner: not yet assigned
For: METHOD OF MANUFACTURING CODE ADDRESS MEMORY CELL	
Commissioner for Patents	OF.

Commissioner for Patents Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to an examination on the merits, please amend the above-identified application as follows.

IN THE ABSTRACT:

Please replace the abstract with the following rewritten abstract.

ABSTRACT OF THE DISCLOSURE

The present invention relates to a method of manufacturing a code address memory (CAM) cell. The present invention uses a dielectric film in which an oxide film and a nitride film between a floating gate and a control gate in a flash memory cell are stacked as a gate insulating film between a semiconductor substrate and a gate in the CAM cell. Therefore, the present invention can reduce the area of a peripheral circuit region and stably secure repaired data since the CAM cell can be stably driven at a low operating voltage and an additional boosting circuit is thus not required.

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